#### Defect Related Switching Field Reduction in Small Magnetic Particle Arrays

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## Sample system



SEM photo: Zofia Vértesy, HAS, Budapest, Hungary

- Single crystal Y<sub>3</sub>Fe<sub>5</sub>O<sub>12</sub>/Gd<sub>3</sub>Ga<sub>5</sub>O<sub>12</sub>
- 42 μm × 42 μm × 3 μm particles,
  12 μm grooves, 1 cm<sup>2</sup> chips
- Strong uniaxial anisotropy, stable axis  $\perp$  to surface

#### Material parameters

- $M_{\rm s}$  = 12.7 kA/m ( $4\pi M_{\rm s}$  = 160 G)
- $H_{\rm u}$  = 170 kA/m (2100 Oe)
- $\sqrt{A/(0.5\mu_0 M_s^2)} = 170$  nm

• 
$$\sqrt{A/K} = 47 \text{ nm}$$

### Pixel magnetization curves



H, Oe









# Defects decorated by AC field Particles' $H_{sw}$ marked, in Oe



#### Switching fields

Geometry	Stoner-Wohlfarth	Micromagnetic
(nm)	(mT)	(mT)
1000 x 1000 x 31.25	177.7	[175,180]
4000 x 4000 x 125	177.7	[175,180]
8000 x 1000 x 250	179.9	[175,180]
1000 x 1000 x 250	183.5	[182,184]
2000 x 2000 x 500	183.5	[180,185]
2000 x 1000 x 1000	187.5	[180,185]

#### Magnetization reversal



Transient state Plate geometry 4  $\mu$ m × 4  $\mu$ m × 125 nm

#### **Reversal nucleates in center**









#### Conclusions

#### **Experimental:**

•  $\mu_0 H_{\rm sw} = 28.5 \text{ mT} \pm 8.5 \text{ mT} \ll \mu_0 H_{\rm u} = 210 \text{ mT}$ 

•  $H_{\rm eff}$  distribution higher and broader than  $H_{\rm sw}$ Simulations:

- Reversal by nucleation + propagation
- Nucleation in center for defect-free plates
- Simple defect model yields  $H_{\rm sw}$  too large
- Linear defect model OK for transitions > 1  $\mu{\rm m}$